

865A RMS Fast Turn-Off Hockey Puk Thyristors

550PEF SERIES

Description

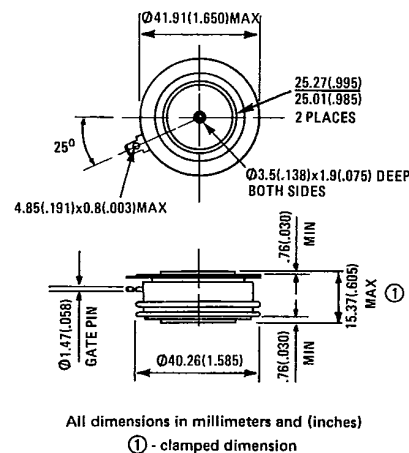
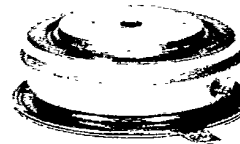
The 550PEF series of fast turn-off thyristors use centre amplified gate junction technology. These devices with their inherently fast switching characteristics combined with their excellent turn-off capabilities will find applications in inverters for UPS systems, AC motor drives, induction heating and choppers.

Features

- Centre Amplified Gate
- High di/dt and dv/dt capabilities
- High frequency operation
- Low switching losses
- High Surge capabilities
- Available up to 1200V V_{RRM} , V_{DRM}
- Fully characterised information
- Choice of turn-off time specification

Major ratings and characteristics

	550PEF.....	Units
$I_T(AV)$	550	A
$I_T(RMS)$	865	A
I_{TSM}	50Hz	6300
	60Hz	6600
I^2_t	50Hz	200,000
	60Hz	181,000
$I^2\sqrt{t}$	2 810 000	$A^2\sqrt{s}$
t_q	20	μs
V_{RRM}	100 to 1200	V
T_J	-40 to 125	$^{\circ}C$



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ELECTRICAL SPECIFICATIONS

Forward conduction

	550PEF.....	Units	Conditions
$I_{T(AV)}$ Average on-state current	550	A	180° conduction, half-sine wave, double side cooled, $T_c = 55^\circ\text{C}$
$I_{T(RMS)}$ Nominal continuous RMS on-state current	865	A	
I_{TRM} Maximum peak repetitive on-state current	5090	A	30° sinusoidal conduction, $T_c = 55^\circ\text{C}$
Mounting force $\pm 10\%$	8920(2000) 4460(1000)	N(lbf)	
I_{TSM} Maximum peak, one cycle non-repetitive on-state current	7500	7000	A $t = 10\text{ms}$ No voltage reapplied Sinusoidal half-wave
	7850	7350	A $t = 8.3\text{ms}$ 100% V_{RRM} reapplied Initial $T_J = 125^\circ\text{C}$
	6300	5900	A $t = 10\text{ms}$ 100% V_{RRM} reapplied
	6600	6150	A $t = 8.3\text{ms}$ 100% V_{RRM} reapplied
I^2t Maximum I^2t for fusing	281 000	245 000	A ² s $t = 10\text{ms}$ No voltage reapplied Initial $T_J = 125^\circ\text{C}$
	257 000	224 000	A ² s $t = 8.3\text{ms}$ 100% V_{RRM} reapplied
	200 000	173 000	A ² s $t = 10\text{ms}$ 100% V_{RRM} reapplied
	181 000	156 000	A ² s $t = 8.3\text{ms}$ 100% V_{RRM} reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	2 810 000	2 450 000	A ² √s $t = 0.1 - 10\text{ms}$, no voltage reapplied
V_{TM} Maximum peak on-state voltage	2.80	V	$T_J = 25^\circ\text{C}$, 180° conduction, $I_{TM} = \pi \times I_{T(AV)}$ (1730A peak)
di/dt Maximum non-repetitive rate of rise of turned on current	800	A/μs	JEDEC STD RS 397, 6.2, 2.6. $T_c = 125^\circ\text{C}$, $V_{DM} = V_{DRM}$, $I_{TM} = 1600\text{A}$ gate source 20V open circuit 20°; $t_r = 0.5\text{ms}$, $t_p = 20\text{ms}$
I_H Maximum holding current	600	mA	$T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load, gate open circuit
I_L Maximum latching current	1000	mA	$T_J = 25^\circ\text{C}$, anode supply = 6V, resistive load

Triggering

P_{GM} Maximum peak gate power	10	W	$t_p \geq 5\text{ms}$
$P_{G(AV)}$ Maximum average gate power	2	W	
I_{GM} Maximum peak gate current	3	A	
V_{GM} Maximum peak gate voltage	20	V	
$-V_{GM}$ Maximum peak negative gate voltage	5	V	
V_{GT} Maximum gate voltage required to trigger	3.0	V	$T_J = -40^\circ\text{C}$ Anode supply = 6V resistive load
	2.5	V	$T_J = 25^\circ\text{C}$
	1.7	V	$T_J = 125^\circ\text{C}$
I_{GT} Maximum gate current required to trigger	400	mA	$T_J = -40^\circ\text{C}$ Anode supply = 6V resistive load
	200	mA	$T_J = 25^\circ\text{C}$
	150	mA	$T_J = 125^\circ\text{C}$
V_{GD} Maximum gate voltage that will not trigger	0.20	V	$T_J = 125^\circ\text{C}$, rated V_{DRM} applied

Switching

t_d Maximum delay time	0.96	μs	$T_J = 25^\circ\text{C}$, $V_D = 0.8 V_{DRM}$, $I_{TM} = 500\text{A}$, gate source 20V open circuit, $R_{\text{source}} = 20\Omega$, resistive load, t_r (pulse rise time) 0.5/μs, $t_p = 20\text{ms}$
t_q Turn-off time	See separate table		
$t_{q(\text{diode})}$ Typical turn-off time with anti parallel diode	20% more than with $VR_{\text{DS}} \geq 50$; see separate tables.	μs	$T_J = 125^\circ\text{C}$, $I_{TM} = 500\text{A}$ for 200μs, $V_R = 1\text{V}$, $di/dt = -25\text{A}/\mu\text{s}$, reapplied $dv/dt = 200\text{V}/\mu\text{s}$ linear to 0.8 V_{DRM} , $V_G = 0$, $R_{gk} = 100\Omega$
Q_{rr} Typical stored charge	47	μC	$T_J = 125^\circ\text{C}$, $I_{TM} = 400\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$

Blocking

dv/dt Minimum critical rate of rise of off-state voltage	500	V/μs	$T_J = 125^\circ\text{C}$, linear to 0.8 V_{DRM} , gate open circuit
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Voltage ratings

Part number	V_{RRM} , maximum repetitive peak reverse voltage $V_g \leq 0$ $T_J = -40^\circ\text{C}$ to 125°C	V_{RSM} , maximum non-repetitive peak reverse voltage $T_J = 25$ to 125°C	V_{DRM} , maximum repetitive peak off-state voltage, gate open circuit $T_J = -40^\circ\text{C}$ to 125°C	I_{RM} , I_{DM} , maximum peak reverse and off-state leakage current at V_{RRM} , V_{DRM} $T_J = 125^\circ\text{C}$, gate open circuit
	V	V	V	mA
550PEF10...	100	200	100	30
550PEF20...	200	300	200	30
550PEF40...	400	500	400	30
550PEF60...	600	700	600	30
550PEF80...	800	900	800	30
550PEF100...	1000	1100	1000	30
550PEF120...	1200	1300	1200	30

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THERMAL AND MECHANICAL SPECIFICATIONS

	550PEF.....	Units	Conditions
T_J Junction operating temperature range	-40 to 125	°C	
T_{stg} Storage temperature range	-40 to 150	°C	
R_{thJC} Maximum thermal impedance, junction to case.	Single side cooled	0.08	K/W DC Operation
	Double side cooled	0.04	
R_{thCS} Maximum thermal resistance, one pole piece to one heat exchanger	0.04 (0.05)	0.03 (0.04)	K/W Mounting surface smooth flat and greased (JEDEC STD RS-397, 7.9.4)
Mounting force $\pm 10\%$	1000	2000	lbf
	4460	8920	N
W Approximate weight	3		oz
	85		g

TURN-OFF TIME TABLE

Part number	Turn off code	t _q Turn off time		Units	Conditions
		typical	max		
550PEF...V..	20	17	20	μ s	reapplied $dv/dt = 20V/\mu s$ linear to 0.8 V _{DRM} $T_J = 125^\circ C$, $I_{TM} = 500A$ for 200 μs $V_R = 50V$ $di/dt = 25A/\mu s$ $V_g = 0V$ $R_{gk} = 100\Omega$
	25	21	25	μ s	
	30	26	30	μ s	
550PEF...W.	25	21	25	μ s	reapplied $dv/dt = 200V/\mu s$ linear to 0.8 V _{DRM}
	30	26	30	μ s	
	35	30	35	μ s	

CODING

To complete code add $V_{RRM}/10$ and required turn-off code. i.e. for a 550PEF..... with $V_{RRM} = 400V$ and $t_q = 25\mu s$ with reapplied $dv/dt = 200 V/\mu s$ complete part number is 550PEF40W25, but for 550PEF..... with same parameters except reapplied $dv/dt = 20V/\mu s$ complete part number is 550PEF40V25.

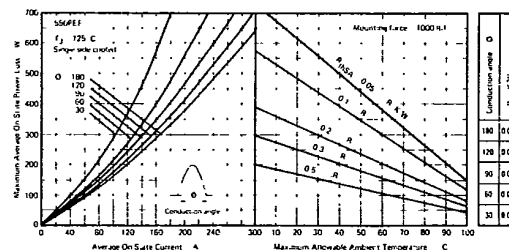
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Use of the Heatsink Selection Nomogram

These nomograms may be used to obtain rapidly the required sink to ambient thermal resistance for a particular application. The above example shows the method.

From the starting point A, the known average on-state current, proceed to point 'B', the operating conduction angle. At this point the maximum average power dissipation may be read off at C. If the maximum ambient temperature is known, proceed vertically from this figure at point E to cross the extension of line C-B at D. The thermal impedance may now be found by taking the lines on either side of point D and choosing the lower figure or by interpolation. The final figure is then found by subtracting the ΔR figure appropriate to the conduction angle in the right hand table.



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Fig. 1 – Current Ratings – sinusoidal waveforms, 50–400Hz

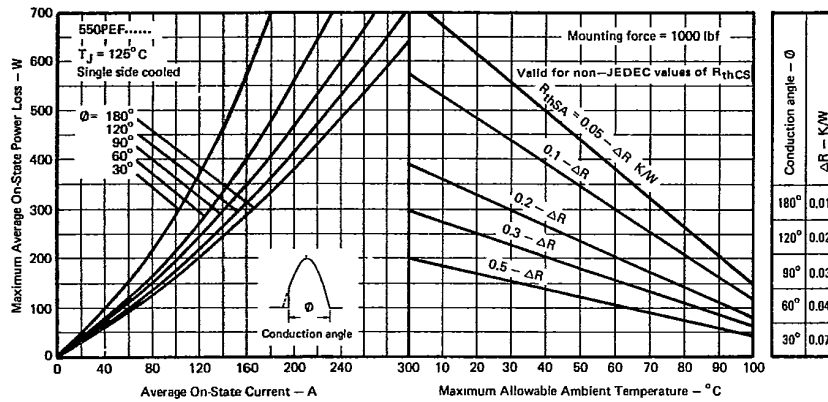


Fig. 2 – Current Ratings – rectangular waveforms, 50–400Hz

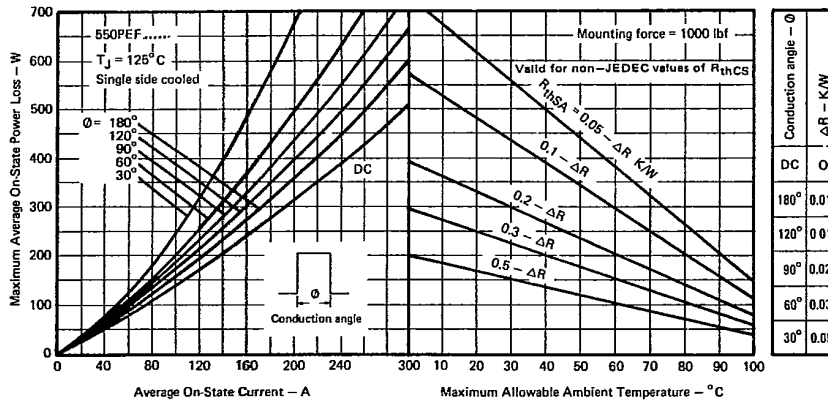
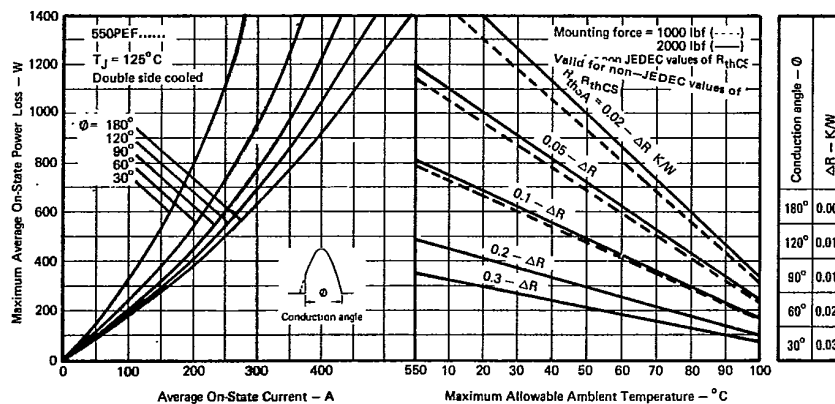


Fig. 3 – Current Ratings – sinusoidal waveforms, 50–400Hz



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Fig. 4 – Current Ratings – rectangular waveforms, 50–400Hz

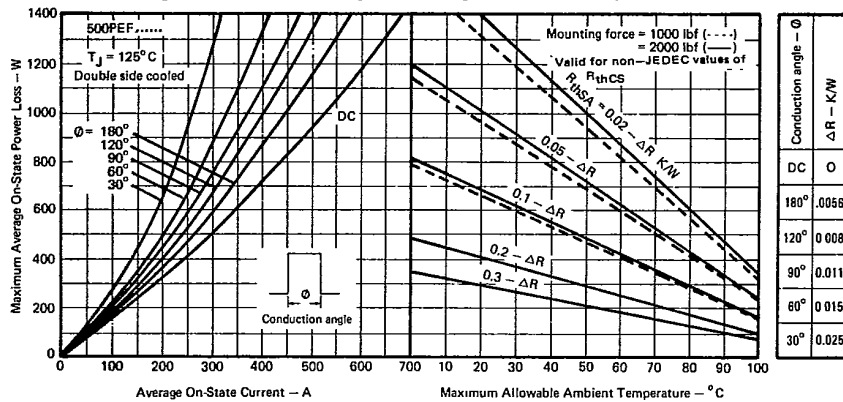


Fig. 5 – Case Temperature Ratings

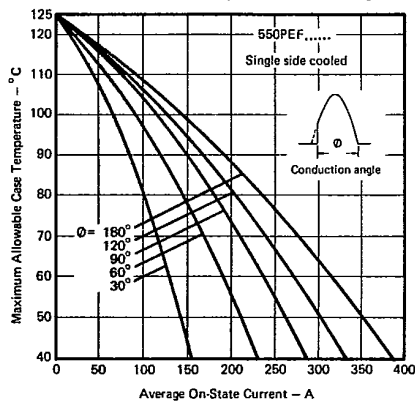


Fig. 6 – Case Temperature Ratings

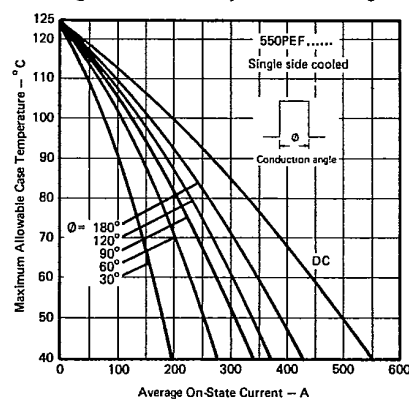


Fig. 7 – Case Temperature Ratings

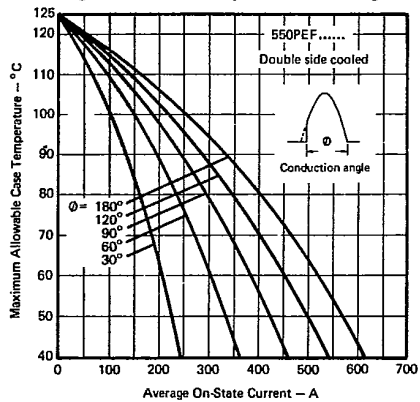
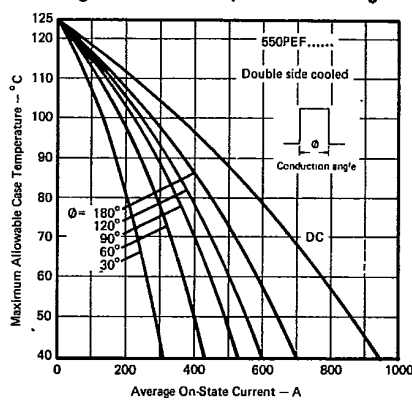
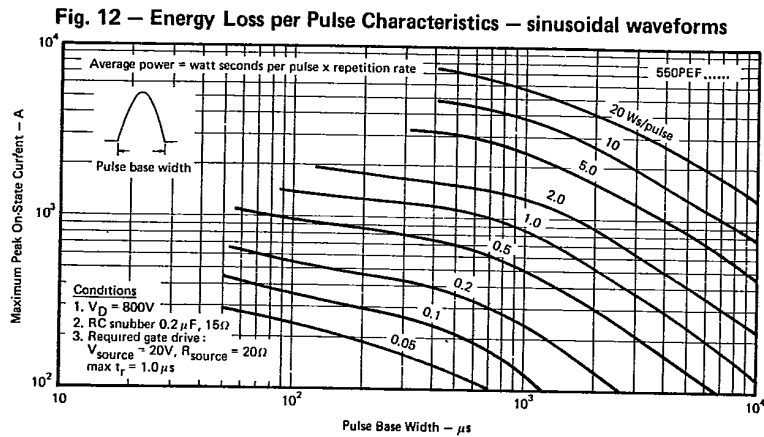
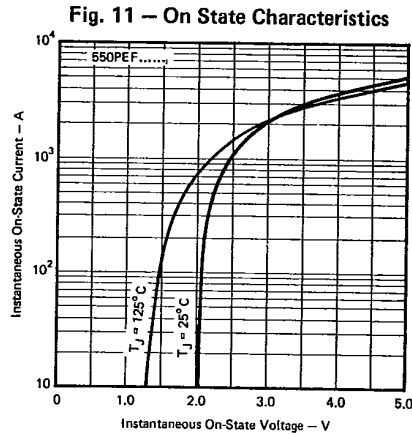
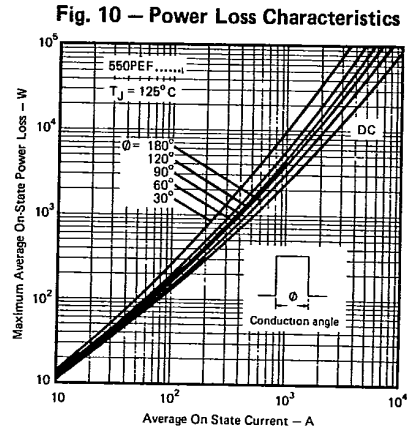
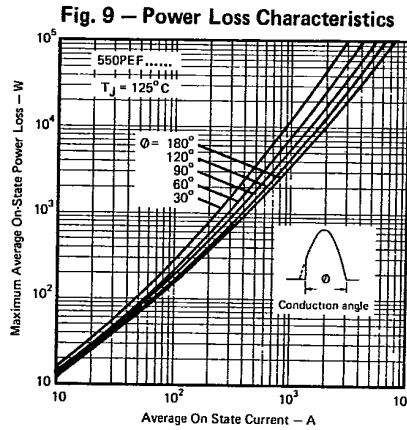


Fig. 8 – Case Temperature Ratings



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Fig. 13 — Energy Loss per Pulse Characteristics — trapezoidal waveforms

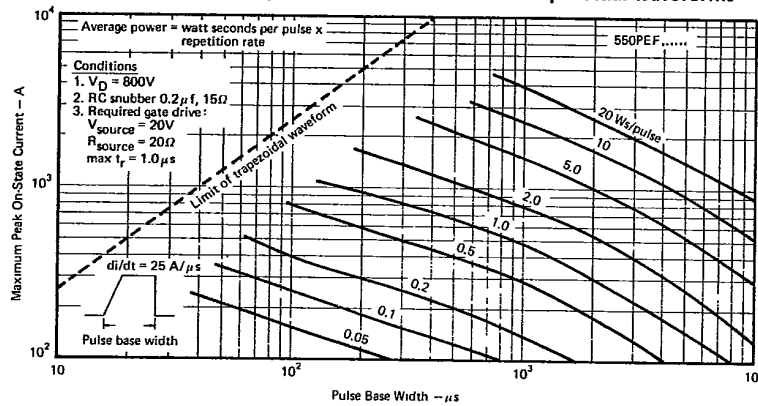


Fig. 14 — Energy Loss per Pulse Characteristics — trapezoidal waveforms

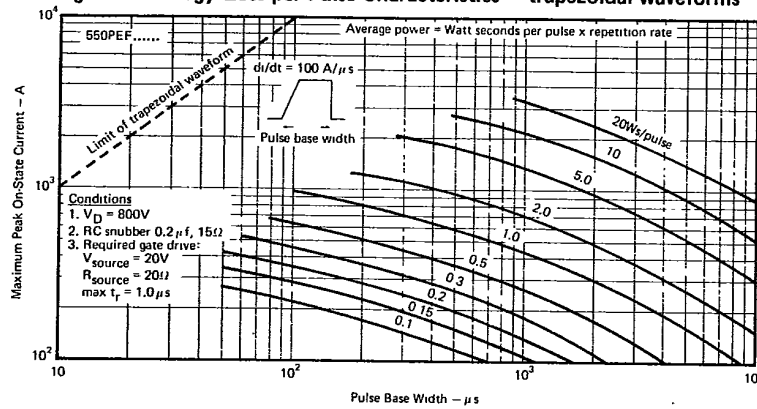
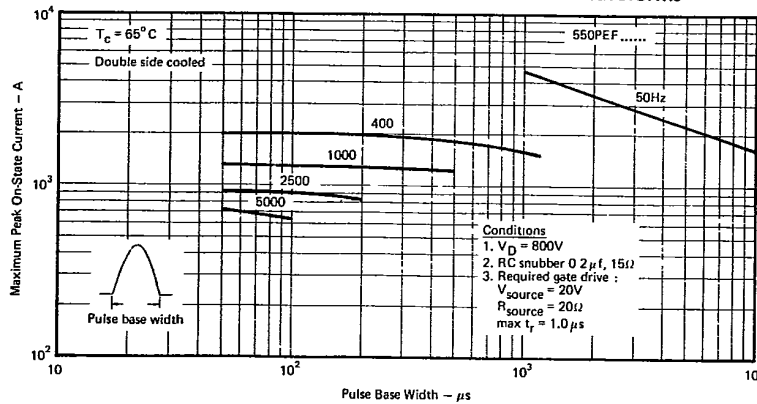


Fig. 15 — Peak On-State vs Pulse Width — sinusoidal waveforms



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Fig. 16 — Peak On-State Current vs Pulse Width — sinusoidal waveforms

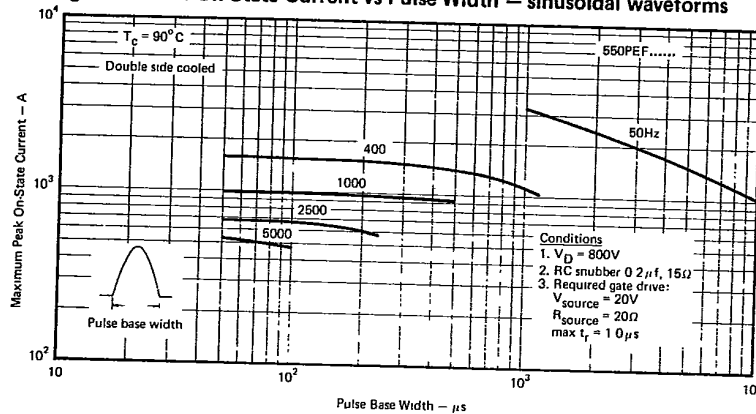


Fig. 17 — Peak On-State Current vs di/dt — trapezoidal waveforms

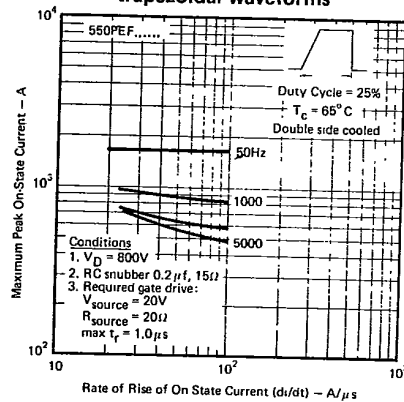


Fig. 18 — Peak On-State Current vs di/dt — trapezoidal waveforms

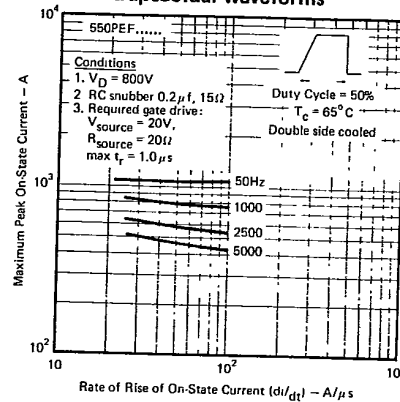


Fig. 19 — Peak On-State Current vs di/dt — trapezoidal waveforms

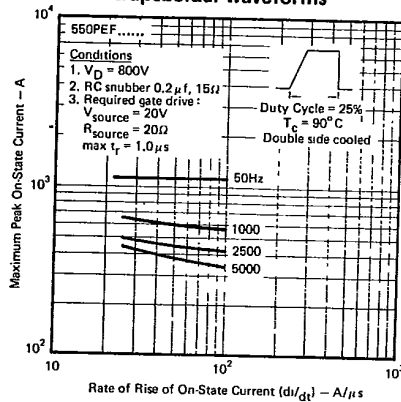
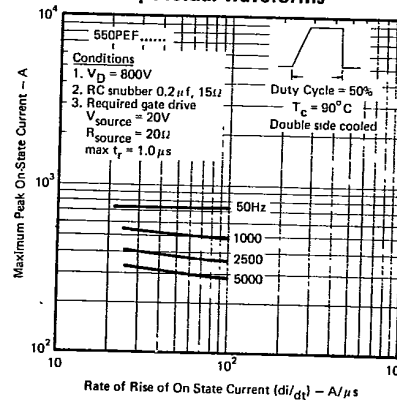
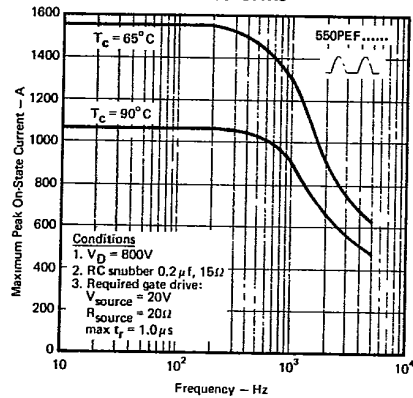
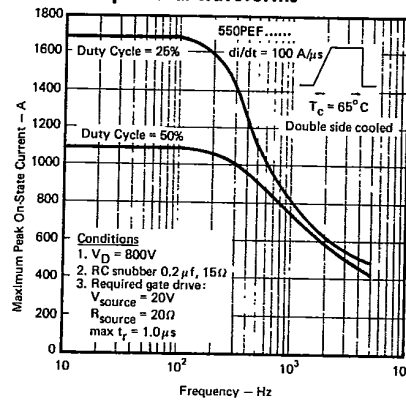
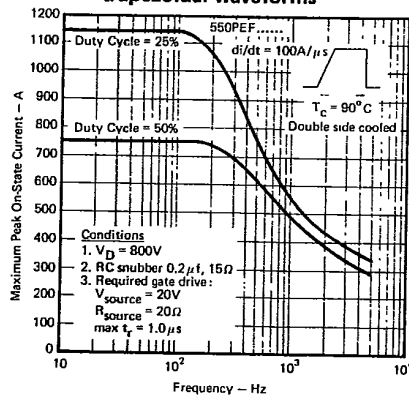
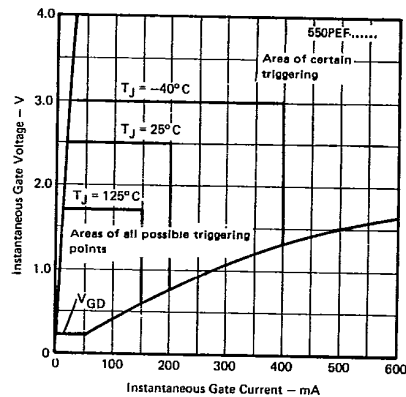
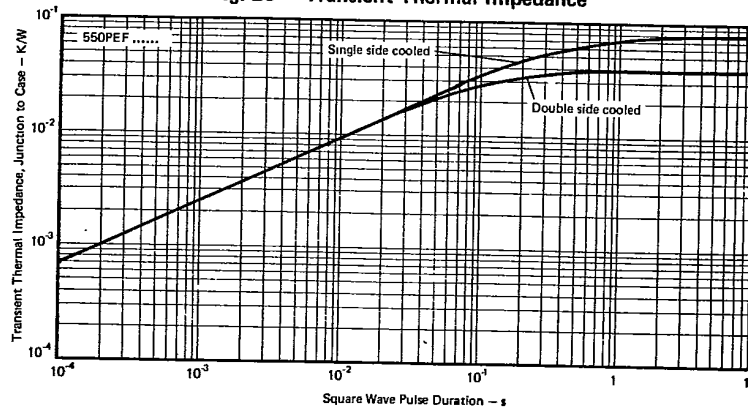


Fig. 20 — Peak On-State Current vs di/dt — trapezoidal waveforms



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Fig. 21 — Peak On-State Current vs Frequency — sinusoidal waveforms**Fig. 22 — Peak On-State Current vs Frequency — trapezoidal waveforms****Fig. 23 — Peak On-State Current vs Frequency — trapezoidal waveforms****Fig. 24 — Gate Characteristics****Fig. 25 — Transient Thermal Impedance**

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Fig. 26 — Non-Repetitive Surge Ratings

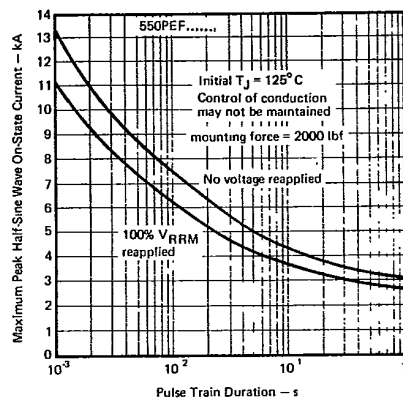


Fig. 27 — Non-Repetitive Surge Ratings

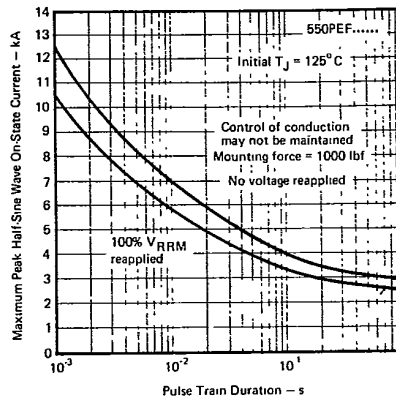


Fig. 28 — Typical Stored Charge Characteristics — sinusoidal waveforms

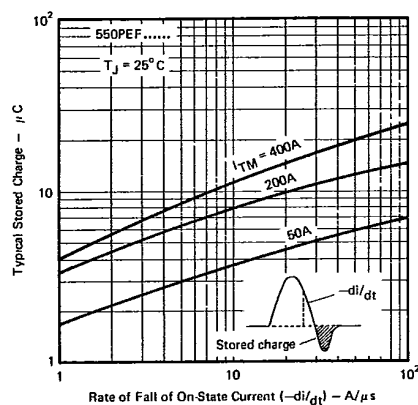
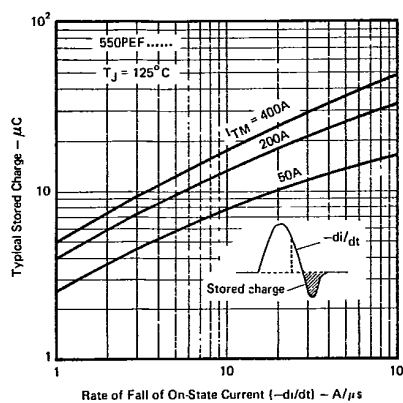


Fig. 29 — Typical Stored Charge Characteristics — sinusoidal waveforms



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